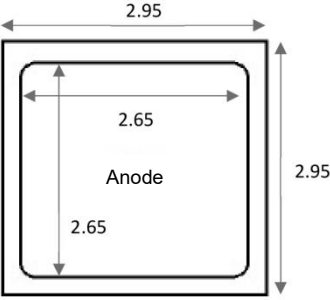


Physical Characteristics

| | |
|---|---|
|  | Die size: 2.95 mm x 2.95 mm (without scribe line) Anode pad open size: 2.65 mm x 2.65 mm Gross die / per 6" wafer = 1647pcs |
| | Main characteristics: $V_{RRM} = 1700V$ $I_F = 10A$ $Q_C = 100nC$ |

Mechanical Data

| Parameter | Parameter |
|--|--------------------------|
| Nominal Back Metal Composition, Thickness | Ti- Ni - Ag(1.4 μ m) |
| Nominal Front Metal Composition, Thickness | Al(4.2 μ m) |
| Wafer Diameter | 150mm |
| Wafer Thickness | 175 μ m |
| Scribe line width | 100 μ m |
| Passivation | Polyimide |

Absolute Maximum Ratings($T_C=25^\circ C$, unless otherwise specified)

| Parameter | Symbol | Test Condition | Value | Unit |
|--------------------------------------|-----------|----------------|-------|------|
| Repetitive Peak Reverse Voltage | V_{RRM} | | 1700 | V |
| Continuous Forward Current | I_F | | 10 | A |
| Non-Repetitive Forward Surge Current | I_{FSM} | $t_P = 10ms$ | 50 | A |
| Repetitive Forward Surge Current | I_{FRM} | $t_P = 10ms$ | 40 | A |

Note: These are stress ratings only and functional operation is not implied. Exposure to absolute maximum ratings for prolonged time periods may affect device reliability.

Electrical Specifications($T_C=25^\circ C$, unless otherwise specified)

| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|--------------------------|--------|----------------------------------|------|------|------|---------|
| Reverse Blocking Voltage | V_R | $I_R = 250\mu A$ | 1700 | | | V |
| Reverse Current | I_R | $V_R = 1700V, T_J = 25^\circ C$ | | 5 | 100 | μA |
| | | $V_R = 1700V, T_J = 175^\circ C$ | | 60 | 200 | |
| Forward Voltage | V_F | $I_F = 10A, T_J = 25^\circ C$ | | 1.6 | 1.9 | V |
| | | $I_F = 10A, T_J = 175^\circ C$ | | 2.5 | 2.9 | |

Note: All characteristics are tested with the parts assembled in TO-247-2 package.